

Title (en)

METHOD AND DEVICE FOR ELECTRICALLY CONTACT-CONNECTING CONNECTION AREAS OF TWO SUBSTRATES

Title (de)

VERFAHREN UND VORRICHTUNG ZUR ELEKTRISCHEN KONTAKTIERUNG VON ANSCHLUSSFLÄCHEN ZWEIER SUBSTRATE

Title (fr)

PROCÉDÉ ET DISPOSITIF DE MISE EN CONTACT ÉLECTRIQUE DE SURFACES DE CONNEXION DE DEUX SUBSTRATS

Publication

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Application

EP 12714202 A 20120130

Priority

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Abstract (en)

[origin: WO2012103868A2] The present invention relates to a method for electrically contact-connecting connection areas of two substrates (6, 7), more particularly of a chip (6) and of a carrier substrate (7). Furthermore, the invention relates to a device for performing a second phase of the method according to the invention. The method according to the invention is effected in two successive phases, wherein, in a first phase, the chip (6) is positioned with its connection areas against connection areas of the substrate (7) and laser energy (5) is applied to the chip (6) at the rear and, in a subsequent second phase, in a housing (3), a flux medium is applied and at the same time a reflow is performed by means of laser energy (5) being applied to the chip (6) at the rear, and a process of purging the housing interior is subsequently performed. The device according to the invention for performing a second phase of the method comprises a carrier table (1) and a housing (3), which together with a top side of the carrier table (1) forms a housing interior, in which the component arrangement is positioned, and also a laser light source (5), which is oriented in such a way that the laser radiation impinges on the first substrate (6) on the rear side.

IPC 8 full level

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CPC (source: EP KR US)

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Citation (search report)

See references of WO 2012103868A2

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